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International
IOR Rectifier

PD - 95042

IRF7329PbF

HEXFET® Power MOSFET

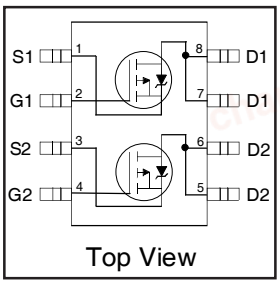
- Trench Technology
- Ultra Low On-Resistance
- Dual P-Channel MOSFET
- Low Profile (<1.8mm)
- Available in Tape & Reel
- Lead-Free

V_{DSS}	$R_{DS(on)}$ max (mΩ)	I_D
-12V	17@V_{GS} = -4.5V	±9.2A
	21@V_{GS} = -2.5V	±7.4A
	30@V_{GS} = -1.8V	±4.6A

Description

New P-Channel HEXFET® power MOSFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the ruggedized device design that HEXFET Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infrared, or wave soldering techniques.



Top View


SO-8

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	-12	V
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ -4.5V	-9.2	A
I_D @ T_A= 70°C	Continuous Drain Current, V_{GS} @ -4.5V	-7.4	
I_{DM}	Pulsed Drain Current ①	-37	
P_D @T_A = 25°C	Power Dissipation ③	2.0	W
P_D @T_A = 70°C	Power Dissipation ③	1.3	
	Linear Derating Factor	16	mW/°C
V_{GS}	Gate-to-Source Voltage	± 8.0	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

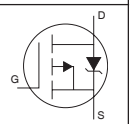
Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	–––	20	°C/W
$R_{\theta JA}$	Junction-to-Ambient ③	–––	62.5	

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Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-12	—	—	V	V_{GS} = 0V, I_D = -250μA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	—	0.007	—	V/°C	Reference to 25°C, I_D = -1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	—	17	mΩ	V_{GS} = -4.5V, I_D = -9.2A ②
		—	—	21		V_{GS} = -2.5V, I_D = -7.4A ②
		—	—	30		V_{GS} = -1.8V, I_D = -4.6A ②
$V_{GS(th)}$	Gate Threshold Voltage	-0.40	—	-0.90	V	V_{DS} = V_{GS}, I_D = -250μA
g_{fs}	Forward Transconductance	25	—	—	S	V_{DS} = -10V, I_D = -9.2A
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	V_{DS} = -9.6V, V_{GS} = 0V
		—	—	-25		V_{DS} = -9.6V, V_{GS} = 0V, T_J = 70°C
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	V_{GS} = -8.0V
	Gate-to-Source Reverse Leakage	—	—	100		V_{GS} = 8.0V
Q_g	Total Gate Charge	—	38	57	nC	I_D = -9.2A
Q_{gs}	Gate-to-Source Charge	—	6.8	10		V_{DS} = -6.0V
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	8.1	12		V_{GS} = -4.5V
$t_{d(on)}$	Turn-On Delay Time	—	10	—	ns	V_{DD} = -6.0V
t_r	Rise Time	—	8.6	—		I_D = -1.0A
$t_{d(off)}$	Turn-Off Delay Time	—	340	—		R_D = 6.0Ω
t_f	Fall Time	—	260	—		V_{GS} = -4.5V ②
C_{iss}	Input Capacitance	—	3450	—	pF	V_{GS} = 0V
C_{oss}	Output Capacitance	—	1000	—		V_{DS} = -10V
C_{rss}	Reverse Transfer Capacitance	—	640	—		f = 1.0MHz

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-2.0	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I_{SM}	Pulsed Source Current (Body Diode) ①	—	—	-37		
V_{SD}	Diode Forward Voltage	—	—	-1.2	V	T_J = 25°C, I_S = -2.0A, V_{GS} = 0V ②
t_{rr}	Reverse Recovery Time	—	50	75	ns	T_J = 25°C, I_F = -2.0A
Q_{rr}	Reverse Recovery Charge	—	48	72	nC	di/dt = -100A/μs ②

Notes:

① Repetitive rating; pulse width limited by max. junction temperature.

② Pulse width ≤ 400μs; duty cycle ≤ 2%.

③ When mounted on 1 inch square copper board.

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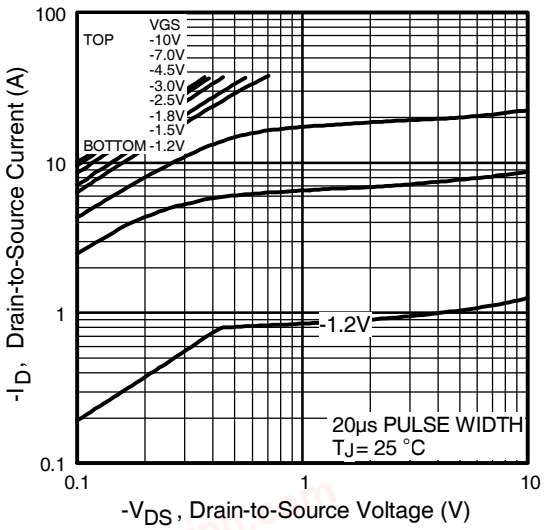


Fig 1. Typical Output Characteristics

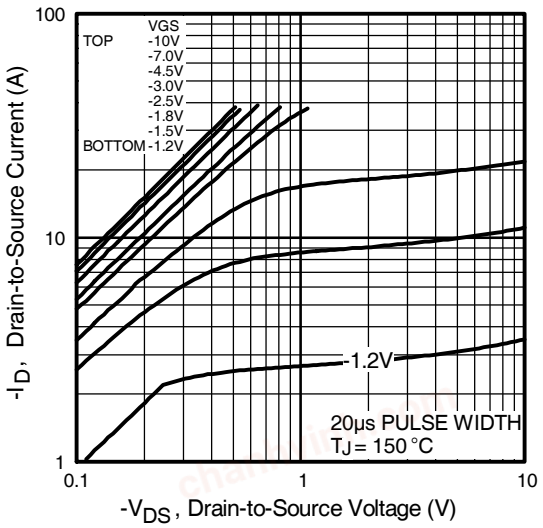


Fig 2. Typical Output Characteristics

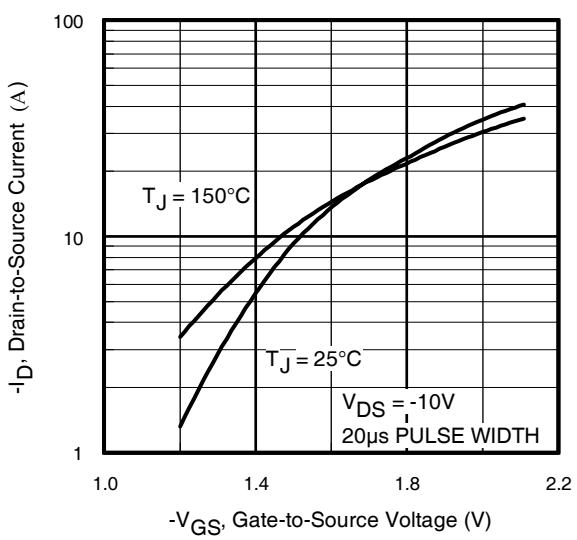


Fig 3. Typical Transfer Characteristics

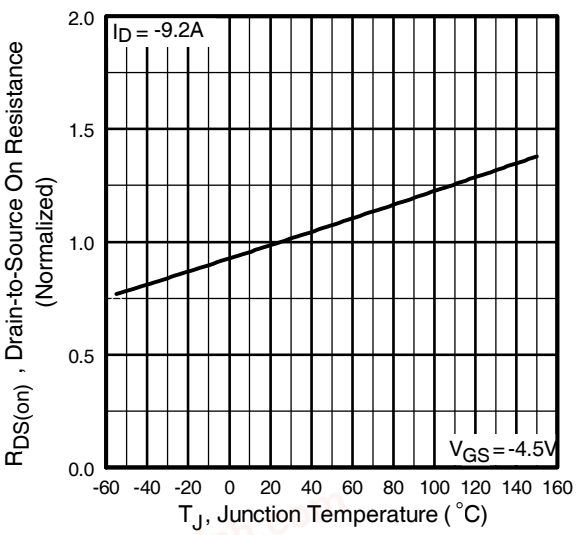


Fig 4. Normalized On-Resistance Vs. Temperature

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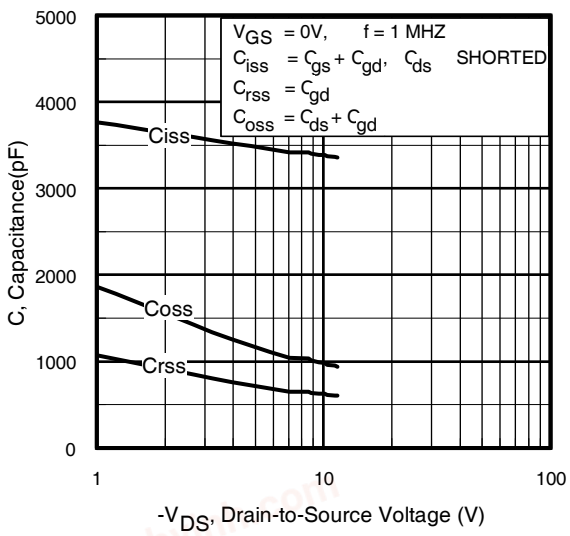


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

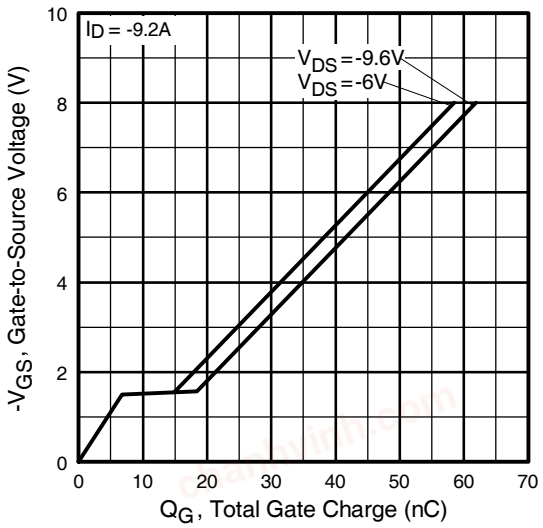


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

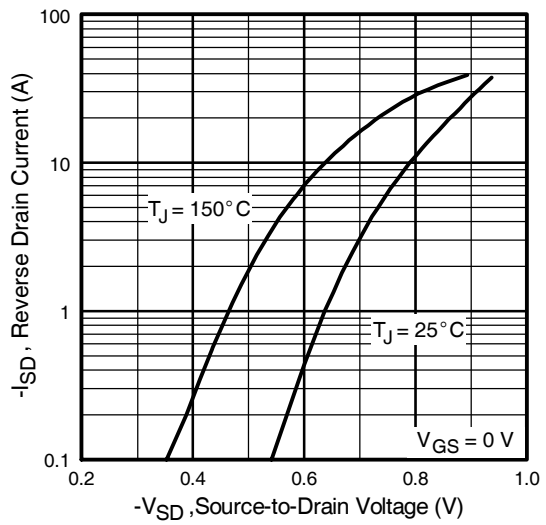


Fig 7. Typical Source-Drain Diode Forward Voltage

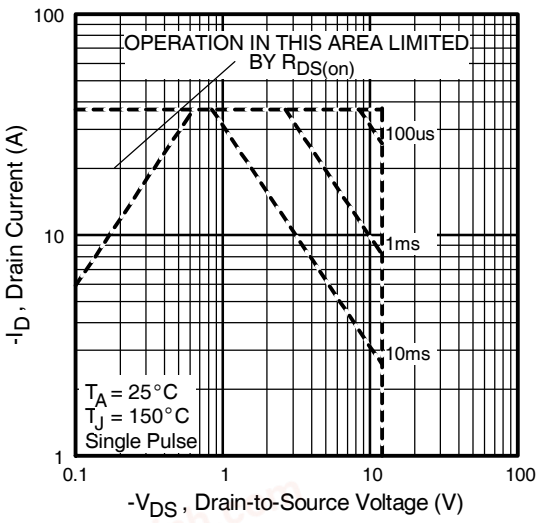


Fig 8. Maximum Safe Operating Area

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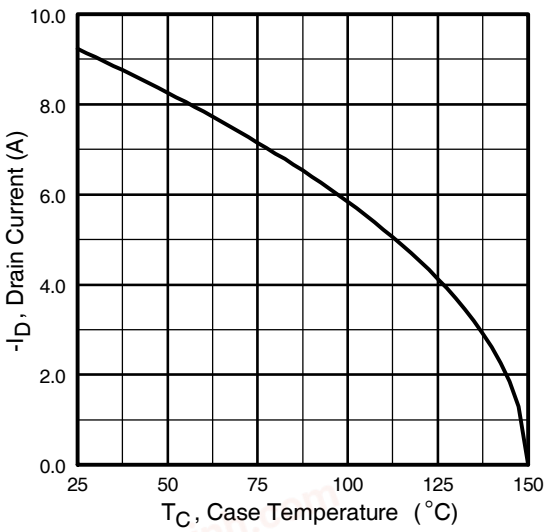


Fig 9. Maximum Drain Current Vs. Case Temperature

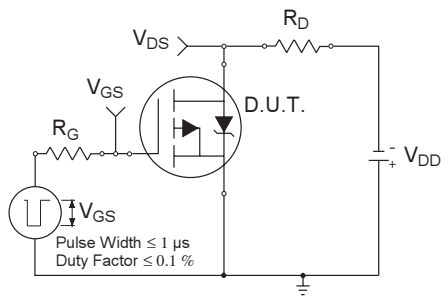


Fig 10a. Switching Time Test Circuit

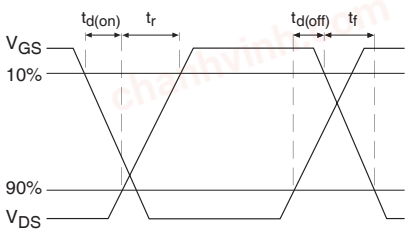


Fig 10b. Switching Time Waveforms

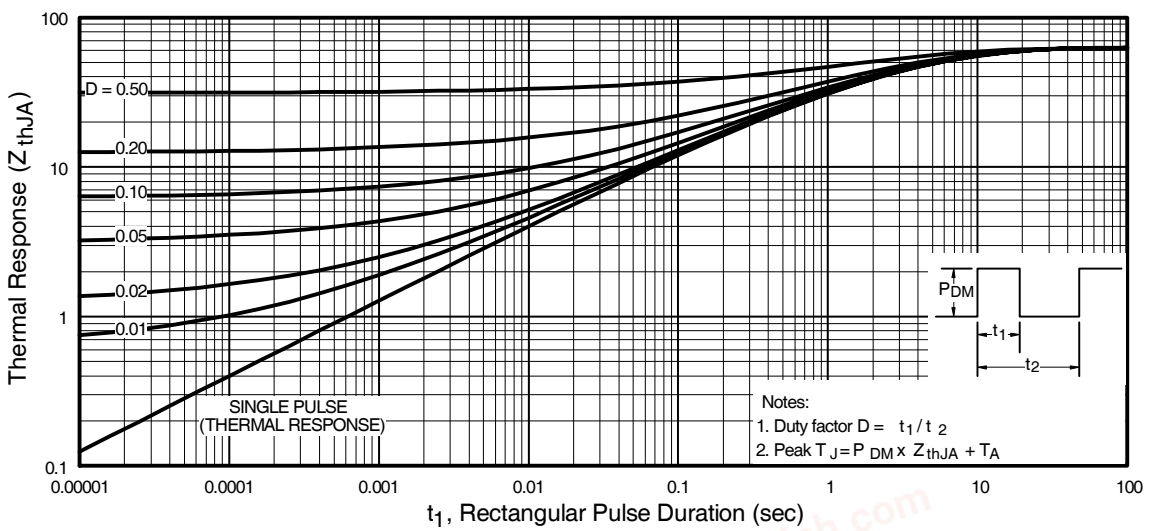


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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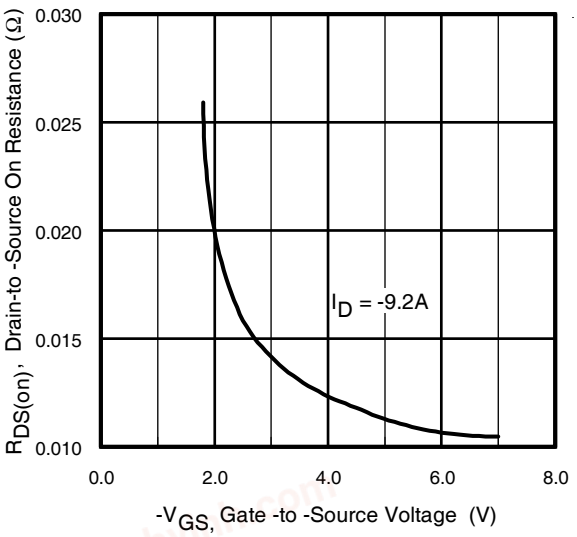


Fig 12. Typical On-Resistance Vs. Gate Voltage

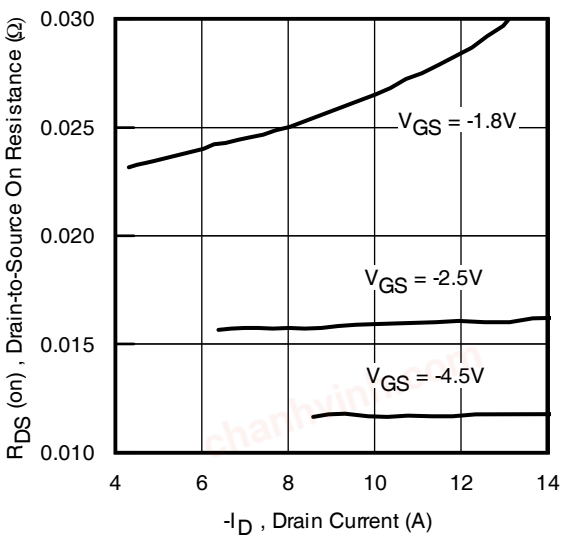


Fig 13. Typical On-Resistance Vs. Drain Current

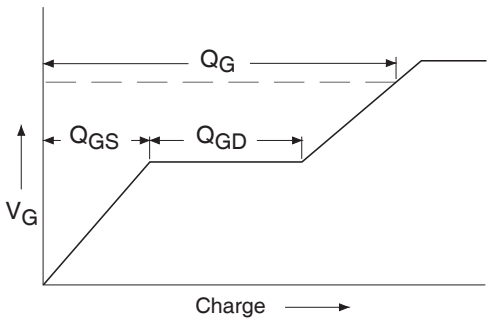


Fig 14a. Basic Gate Charge Waveform

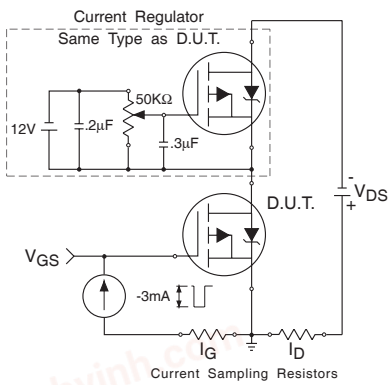


Fig 14b. Gate Charge Test Circuit

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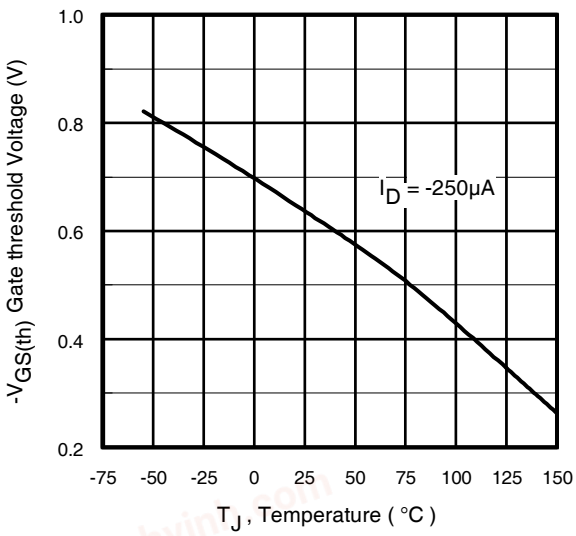


Fig 15. Typical Vgs(th) Vs. Junction Temperature

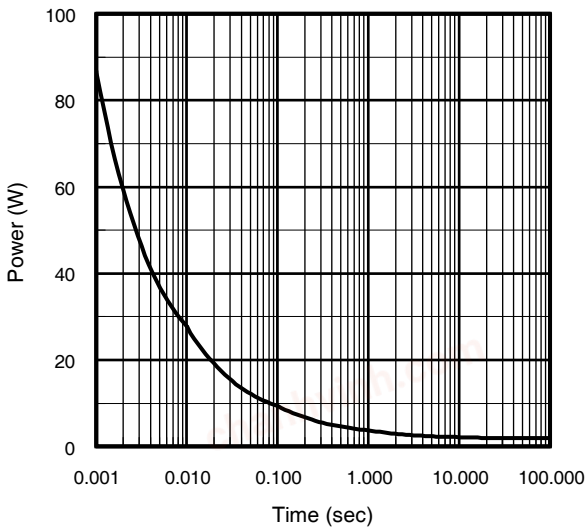
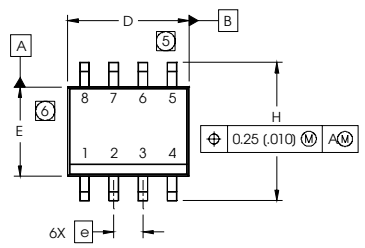


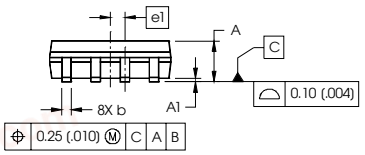
Fig 16. Typical Power Vs. Time

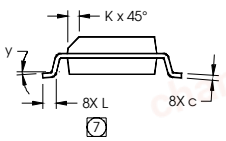
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SO-8 Package Outline

Dimensions are shown in milimeters (inches)







DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°

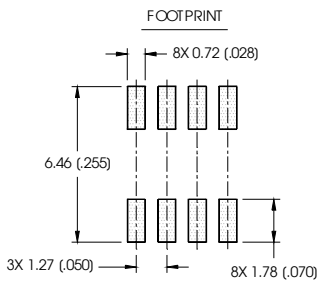
NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS (INCHES).
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.

5 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.15 (.006).

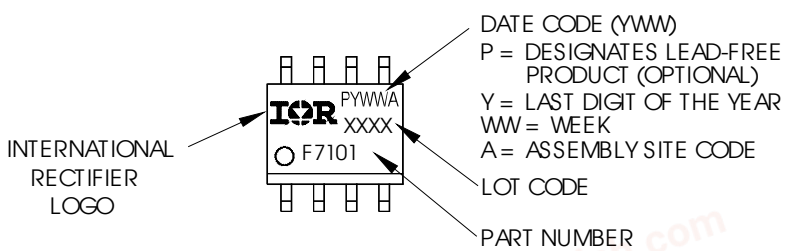
6 DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS. MOLD PROTRUSIONS NOT TO EXCEED 0.25 (.010).

7 DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO A SUBSTRATE.



SO-8 Part Marking Information (Lead-Free)

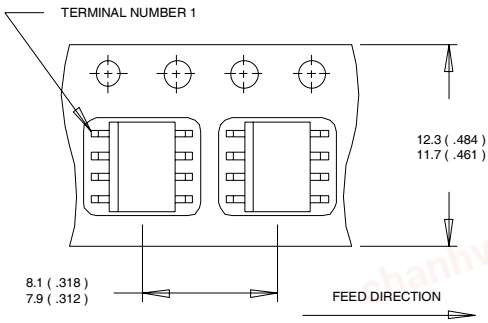
EXAMPLE: THIS IS AN IRF7101 (MOSFET)



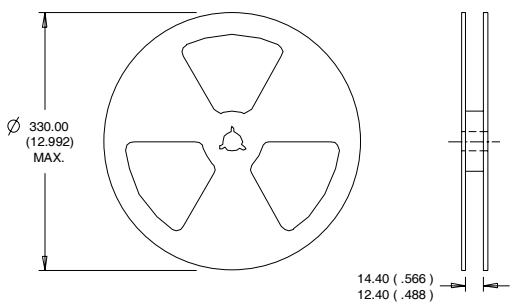
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SO-8 Tape and Reel

Dimensions are shown in milimeters (inches)



NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualification Standards can be found on IR's Web site.

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